

Name (in Arabic): محمد عبد الوهاب

Electronics I EE0903261

Answer all questions in ink.

Second Exam

Exam Duration: 120 min.

Reg. #: 0094557

Date: May 13, 2014

Mark out of 30:

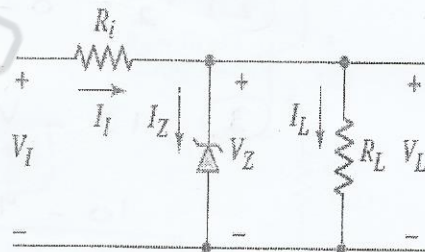
22

(1) محمد

Q.1 a) Consider the zener diode circuit shown. Let  $V_I = 57\text{ V}$ ,  $V_Z = 12\text{ V}$ , the power rating of the diode is  $3\text{ W}$ ,  $R_i = 150\ \Omega$ ,  $r_z = 0\ \Omega$ , and the minimum diode current is  $25\text{ mA}$ .

i) Calculate the maximum diode current.

ii) What is the power dissipated in  $R_i$ . What maximum value of  $R_L$  ensures safe operation of the diode. What minimum value of  $R_L$  results in minimum diode current.



~~$I_{Zmin} = 0.1 I_{Zmax} \Rightarrow I_{Zmax} = 250\text{ mA}$~~

~~$I_{Zmin} = 0.1 I_{Zmax} \Rightarrow I_{Zmax} = 250\text{ mA}$~~

$$P_{Ri} = \frac{(V_I - V_Z)^2}{R_i I_{Zmin}} = \frac{2025}{150 \cdot 0.025} = 540\text{ W}$$

~~$P_{Ri} = 4050\text{ W}$~~

$$P_{Ri} = 13.5\text{ W}$$

$$I_{Lmin} = \frac{3}{12} = 0.25\text{ A}$$

$$150 = \frac{57 - 12}{0.025 + I_{Lmax}} \Rightarrow I_{Lmax} = 0.275\text{ A}$$

max. value of  $R_L$  is at  $I_{Lmin}$ :

$$V_L = 12 = I_{Lmin} R_{Lmax} \Rightarrow R_{Lmax} = \frac{12}{0.25} = 48\ \Omega$$

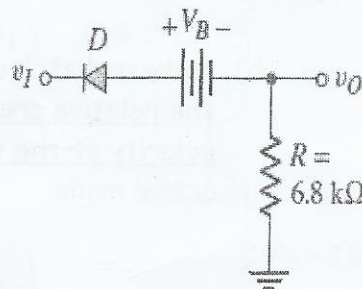
$$R_{Lmin} = \frac{12}{I_{Lmax}} = \frac{12}{0.275} = 43.64\ \Omega$$

b) Consider the circuit shown.

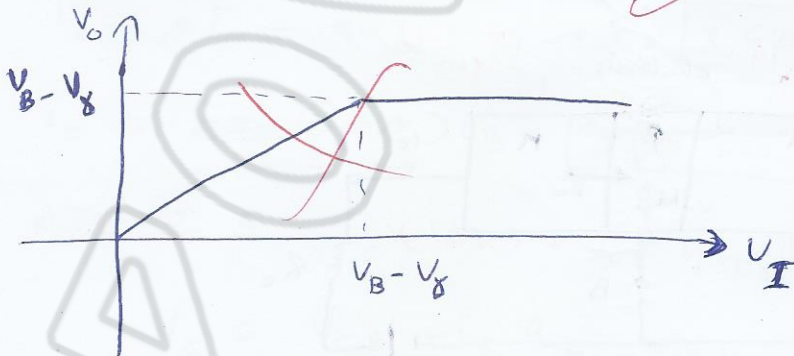
Obtain the condition on  $V_I$ ,  $V_B$ , and  $V_Y$  for the diode to be ON, Hence write the value of  $v_o$  in this case. Make a sketch of  $v_o$  against  $v_I$ .

$$+V_I = V_D + V_B + \frac{V_D + V_B + V_Y}{R}$$

the condition is to be  $V_I \geq V_B + V_Y$



$$v_o = -V_B + V_D + V_Y$$



Q2) a) Consider the circuit shown. Determine  $V_1$ ,  $V_2$ , and Calculate the values of the three resistors assuming the diodes are all ON with  $I_{D1} = 0.2 \text{ mA}$ ,  $I_{D2} = 0.3 \text{ mA}$ , and  $I_{D3} = 0.5 \text{ mA}$ . Let  $V_\gamma = 0.7 \text{ V}$ .

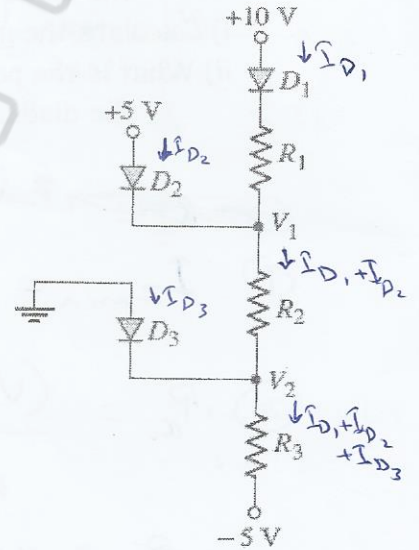
①  $V_1 = 5 - V_\gamma = 5 - 0.7 = \boxed{4.3 \text{ V}}$

②  $V_2 = 0 - 0.7 = \boxed{-0.7 \text{ V}}$

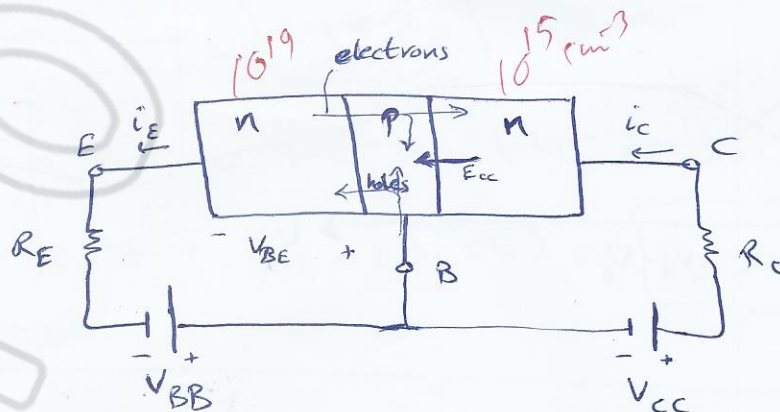
③  $10 - V_1 = V_\gamma + I_{D1} R_1$   
 $10 - 4.3 = 0.7 + 0.2 \times 10^{-3} (R_1)$   
 $\therefore R_1 = \boxed{25 \text{ k}\Omega}$

④  $V_1 - V_2 = (I_{D1} + I_{D2}) R_2$   
 $R_2 = \frac{4.3 + 0.7}{0.5 \times 10^{-3}} = \boxed{10 \text{ k}\Omega}$

⑤  $V_2 - (-5) = (I_{D1} + I_{D2} + I_{D3}) R_3$   
 $R_3 = \frac{-0.7 + 5}{1 \times 10^{-3}} = \boxed{4.3 \text{ k}\Omega}$



b) Make a sketch of a npn transistor implemented on a slice of silicon. Clearly showing the relative areas of each region, the carrier concentration in each region and the polarity of the voltage sources connected to drive the transistor in the forward active mode.



Q3 a) Consider the transistor circuit shown. Assuming  $V_{\gamma} = 0.7 \text{ V}$ , and  $\beta = 99$ , calculate  $V_{CE}$  and verify if the transistor is indeed in the forward active mode.

~~$i_B = 0$~~

$$0 = i_B (10 \text{ k}) + V_{\gamma} + i_E (4 \text{ k}) - 8$$

$$0 = i_B (10 \text{ k}) + 0.7 + (1 + \beta) i_B (4 \text{ k}) - 8$$

$$7.3 = i_B (10 \text{ k} + 400 \text{ k}) \Rightarrow i_B = 17.8 \mu\text{A}$$

~~$i_C = \beta i_B = 99 (17.8 \mu) \Rightarrow i_C = 1.76 \text{ mA}$~~

$$i_E = (1 + \beta) i_B = 100 (17.8 \mu) \Rightarrow i_E = 1.78 \text{ mA}$$

~~$V_{CE} = 8 = i_C (4 \text{ k}) + V_{CE} + i_E (4 \text{ k}) - 8 \Rightarrow V_{CE} = 1.84 \text{ V}$~~

$$V_{CE} = V_{CB} + V_{BE} \Rightarrow 1.84 = V_{CB} + 0.7 \Rightarrow V_{CB} = 1.14 \text{ V} \Rightarrow V_{BC} = -1.14 \text{ V} \Rightarrow \text{R.B.}$$

$\therefore \text{B-C: R.B. \& B-E: F.B.} \Rightarrow \therefore \text{in FAM}$

b) Consider the transistor circuit shown. Assuming  $V_{\gamma} = 0.7 \text{ V}$ , and  $\beta = 99$ , calculate  $V_C$  and  $V_{CE}$ .

$$5 = i_C (10 \text{ k}) + i_B (20 \text{ k}) + V_{\gamma} + i_E (2 \text{ k})$$

$$5 = \beta i_B (10 \text{ k}) + i_B (20 \text{ k}) + V_{\gamma} + (1 + \beta) i_B (2 \text{ k})$$

$$i_B = \frac{5 - 0.7}{10^3 \times 1210} = 3.55 \mu\text{A}$$

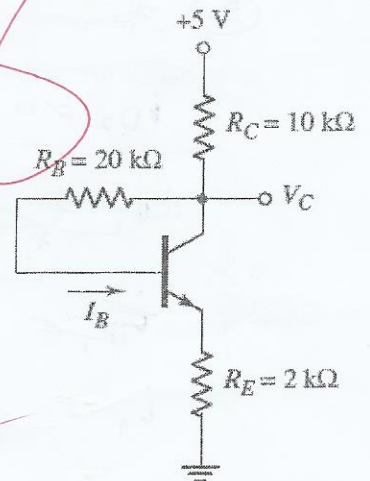
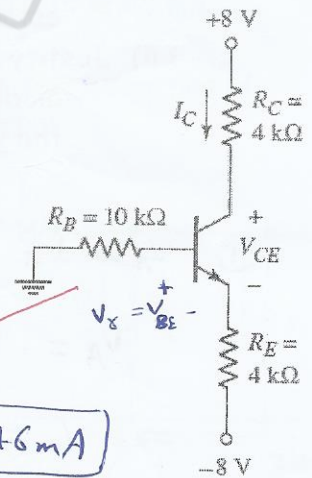
$$i_C = \beta i_B = 99 (3.55 \mu) = 3.52 \times 10^{-4} \text{ A}$$

$$i_E = (1 + \beta) i_B = 3.55 \times 10^{-4} \text{ A}$$

~~$V_C = 5 = i_C (10 \text{ k}) + V_{CE} + i_E (2 \text{ k}) \Rightarrow V_{CE} = 0.77 \text{ V}$~~

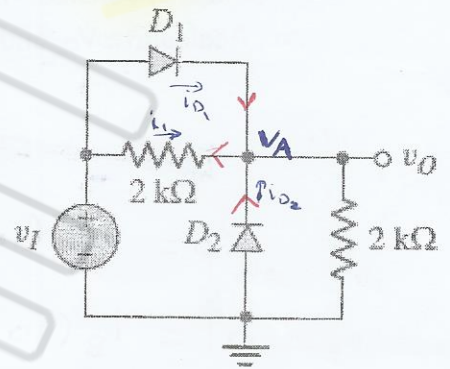
$$V_C = V_{CE} + i_E R_E \Rightarrow V_C = 0.77 + 3.55 \times 10^{-4} (2 \times 10^3)$$

$$\therefore V_C = 1.48 \text{ V}$$



Q4 Consider the circuit shown with  $V_I = 5V$ , and  $V_\gamma = 0.7V$ .

- By considering KCL at the  $v_o$  node or otherwise establish why the two diodes cannot be both ON.
- Justify the possibility of diode  $D_1$  being ON, and diode  $D_2$  being OFF. If this case is valid, calculate the values of the currents involved.



① ~~If~~ Both  $D_1$  &  $D_2$  are ON:

$$V_A = -0.7V$$

$$\Rightarrow v_o = -0.7 - (-0.7) = 0V?$$

$$i_{D1} + \frac{-0.7 - 5}{2k} + i_{D2} = 0$$

$$i_{D1} + i_{D2} = 2.85mA$$

$$\text{but } i_1 = \frac{+0.7 + 5}{2k} = 2.85mA$$

$\therefore$  ~~both~~  $D_1$  &  $D_2$  can't be ON.

$$5 + 0.7 = 2k(i) \\ i = ()$$

$$i_{D1} + \frac{V_A - 5}{2k} = i_{D2}$$

$$i_{D1} + i_{D2} = \frac{5 - 0.7}{2k}$$

$$2.15mA \\ 5 + 0.7 = i(2k) \\ i =$$

② For  $D_1$  ON &  $D_2$  OFF:

$$i_{D2} = 0$$

~~$$i_{D1} = \frac{0.7}{2k} = 0.35mA$$~~

$$i_{D1} = 2.15mA$$

$$i_1 = \frac{0.7}{2k} = 0.35mA$$

~~$$i_{D1} = 5 - 0.7 - 2k(i_{D1} + 0.35mA)$$~~

$$5 = 0.7 + (i_{D1} + i_1)(2k) \Rightarrow i_{D1} = 1.8mA$$

3.5